



YJN180G10HJ

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	100V
I_D	180A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	4.3m
100% EAS Tested	
100%	



Typical Electrical and Thermal Characteristics Diagrams

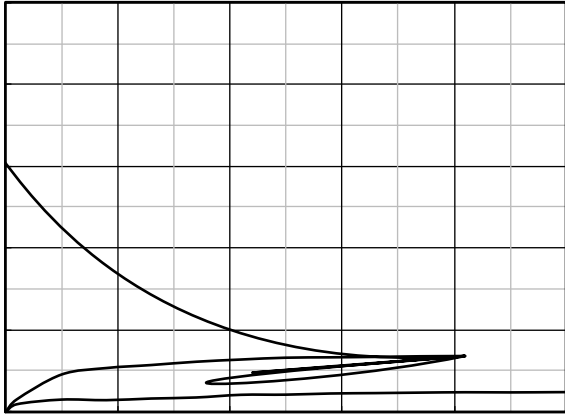


Figure 1. Output Characteristics

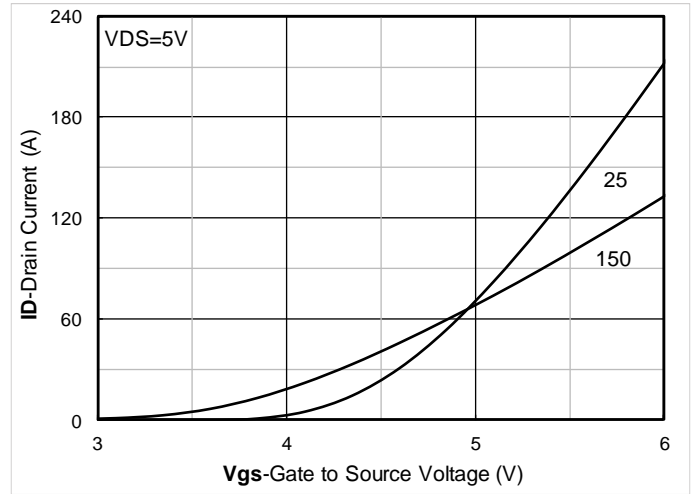


Figure 2. Transfer Characteristics



YJN180G10HJ

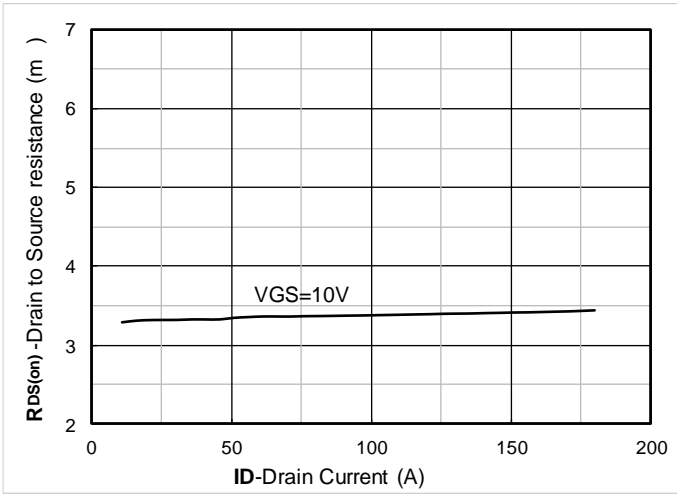


Figure 7. $R_{DS(on)}$ VS Drain Current

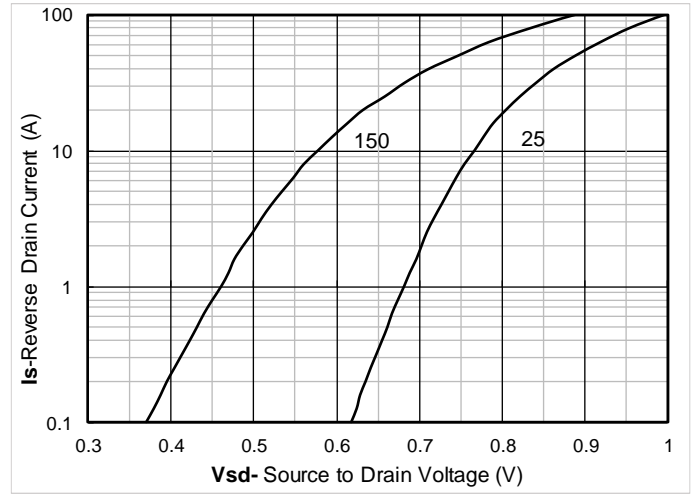


Figure 8. Forward characteristics of reverse diode

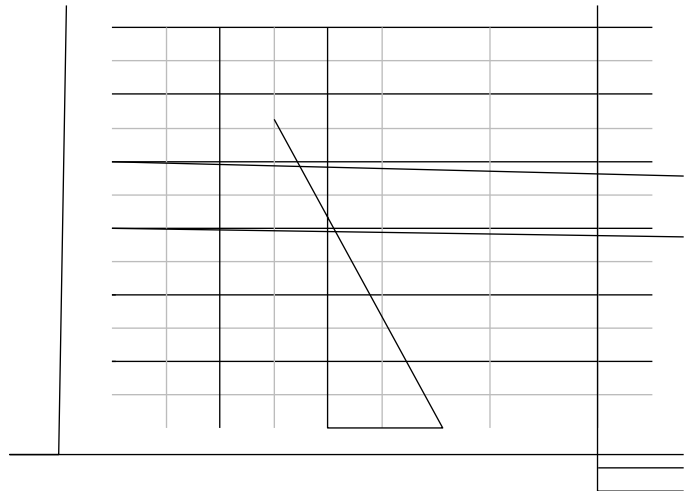


Figure 9. Normalized breakdown voltage

Figure 10. Normalized Threshold voltage

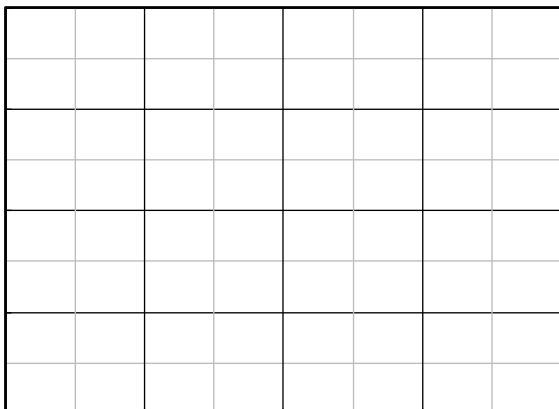


Figure 11. Current dissipation

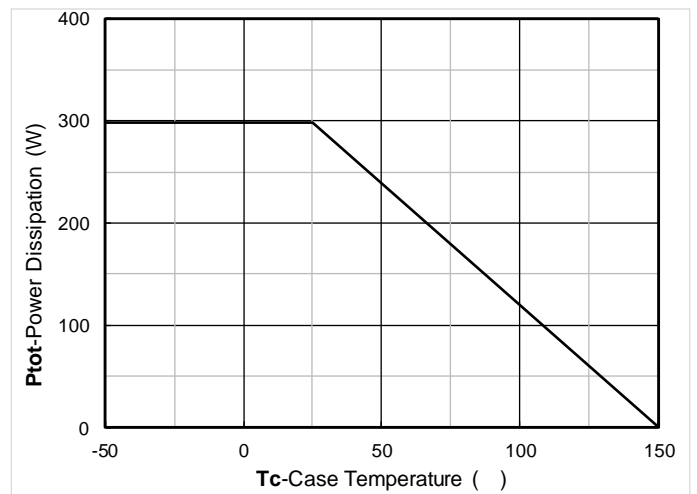


Figure 12. Power dissipation

YJN180G10HJ

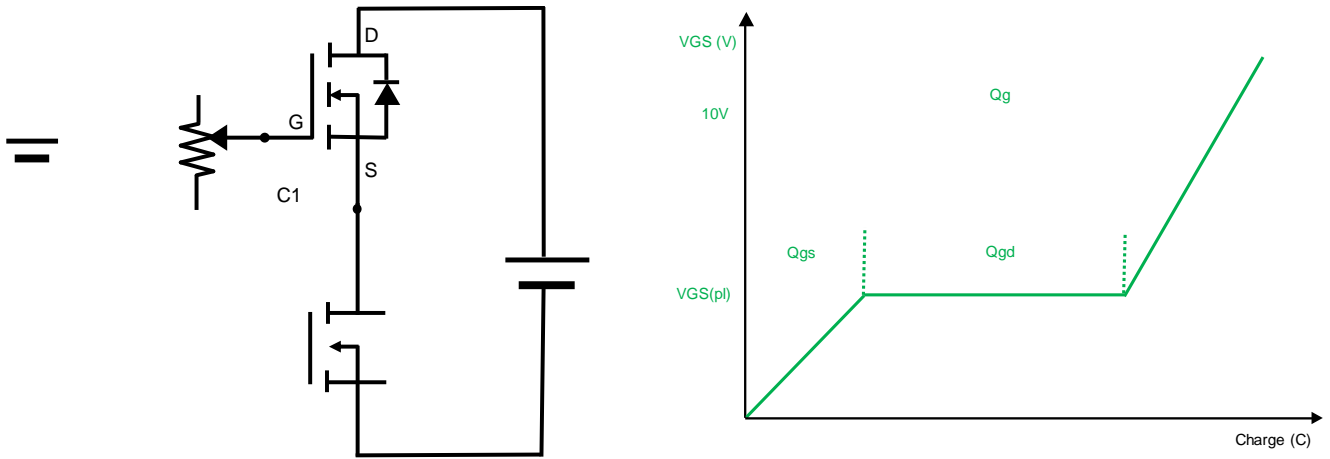


Figure B. Gate Charge Test Circuit & Waveform

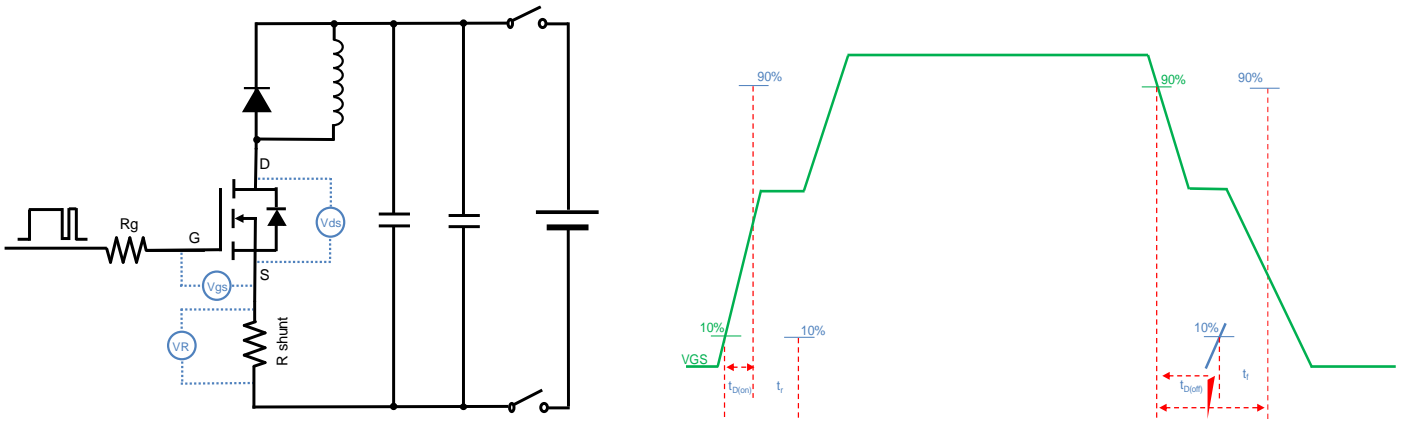


Figure C. Resistive Switching Test Circuit & Waveform



Figure D. Diode Recovery Test Circuit & Waveform



TO-247AB Package information

TO-247AB	
Dim	Min



YJN180G10HJ

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <http://www.21yangjie.com> , or consult your nearest Yangjie's sales office for further assistance.